

N-channel 60 V, 0.22 Ω typ., 38 A, STripFET™ II Power MOSFET in a TO-220 package

Datasheet – production data

Features

Order code	V _{DS}	R _{DS(on)}	I _D
STP45NF06	60 V	0.028 Ω	38 A

- Typical R_{DS(on)} = 0.022 Ω
- Exceptional dv/dt capability
- 100% avalanche tested
- Standard threshold drive

Applications

- Switching application

Description

This Power MOSFET has been developed using STMicroelectronics' unique STripFET process, which is specifically designed to minimize input capacitance and gate charge. This renders the device suitable for use as primary switch in advanced high-efficiency isolated DC-DC converters for telecom and computer applications, and applications with low gate charge driving requirements.

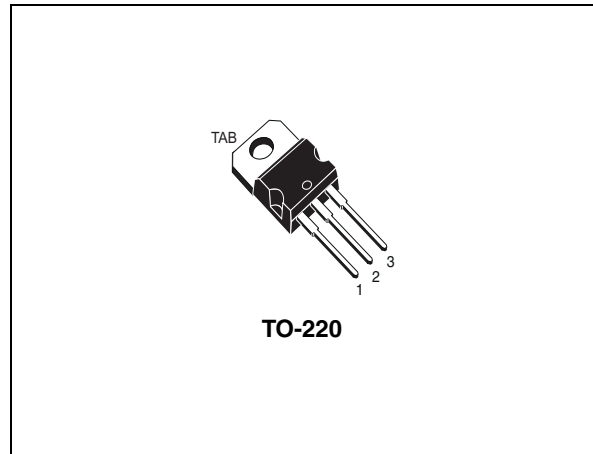


Figure 1. Internal schematic diagram

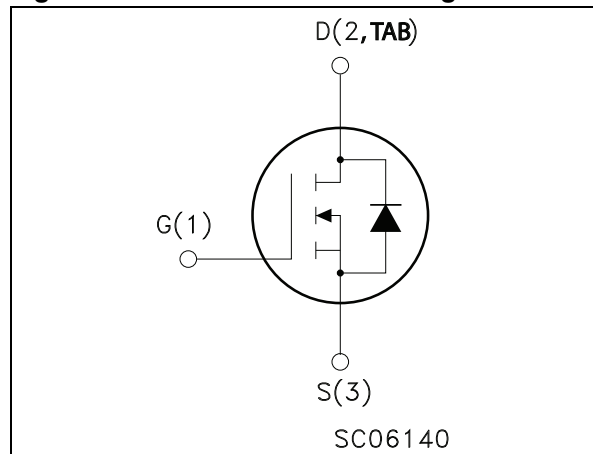


Table 1. Device summary

Order code	Marking	Package	Packaging
STP45NF06	45NF06	TO-220	Tube

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1 Electrical ratings

Table 2. Absolute maximum ratings

Symbol	Parameter	Value	Unit
V_{DS}	Drain-source voltage	60	V
V_{DGR}	Drain-gate voltage ($R_{GS}=20\text{ k}\Omega$)	60	V
V_{GS}	Gate-source voltage	± 20	V
I_D	Drain current (continuous) at $T_C = 25\text{ }^\circ\text{C}$	38	A
I_D	Drain current (continuous) at $T_C = 100\text{ }^\circ\text{C}$	26	A
$I_{DM}^{(1)}$	Drain current (pulsed)	152	A
P_{TOT}	Total dissipation at $T_C = 25\text{ }^\circ\text{C}$	80	W
	Derating factor	0.53	W/ $^\circ\text{C}$
$dv/dt^{(2)}$	Peak diode recovery voltage slope	7	V/ns
T_{stg}	Storage temperature	- 65 to 175	$^\circ\text{C}$
T_j	Max. operating junction temperature	175	$^\circ\text{C}$

1. Pulse width limited by safe operating area

2. $I_{SD} \leq 38\text{ A}$, $di/dt \leq 300\text{ A}/\mu\text{s}$; $V_{DS(\text{peak})} < V_{(BR)DSS}$; $V_{DD}=80\% V_{(BR)DSS}$

Table 3. Thermal data

Symbol	Parameter	Value	Unit
$R_{thj\text{-case}}$	Thermal resistance junction-case max	1.88	$^\circ\text{C}/\text{W}$
$R_{thj\text{-amb}}^{(1)}$	Thermal resistance junction-ambient max	35	$^\circ\text{C}/\text{W}$

1. When mounted on 1 inch² FR-4, 2 Oz copper board.

Table 4. Avalanche characteristics

Symbol	Parameter	Value	Unit
I_{AR}	Avalanche current, repetitive or not repetitive (pulse width limited by $T_{j\text{max}}$)	38	A
E_{AS}	Single pulse avalanche energy (starting $T_J = 25\text{ }^\circ\text{C}$, $I_D = I_{AR}$; $V_{DD}=50\text{ V}$)	135	mJ

2 Electrical characteristics

($T_C = 25\text{ °C}$ unless otherwise specified).

Table 5. On /off states

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source breakdown voltage	$I_D = 250\text{ mA}$, $V_{GS} = 0$	60			V
I_{DSS}	Zero gate voltage drain current ($V_{GS} = 0$)	$V_{DS} = 60\text{ V}$ $V_{DS} = 60\text{ V}$, $T_C = 125\text{ °C}$			1 10	μA μA
I_{GSS}	Gate-body leakage current ($V_{DS} = 0$)	$V_{GS} = \pm 20\text{ V}$			± 100	nA
$V_{GS(th)}$	Gate threshold voltage	$V_{DS} = V_{GS}$, $I_D = 250\text{ }\mu\text{A}$	2	3	4	V
$R_{DS(on)}$	Static drain-source on-resistance	$V_{GS} = 10\text{ V}$, $I_D = 19\text{ A}$		0.022	0.028	Ω

Table 6. Dynamic

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$g_{fs}^{(1)}$	Forward transconductance	$V_{DS} > I_{D(on)} * R_{DS(on)max}$, $I_D = 19\text{ A}$	-	24		S
C_{iss} C_{oss} C_{rss}	Input capacitance Output capacitance Reverse transfer capacitance	$V_{DS} = 25\text{ V}$, $f = 1\text{ MHz}$, $V_{GS} = 0$	-	1730 215 63		pF pF pF
Q_g Q_{gs} Q_{gd}	Total gate charge Gate-source charge Gate-drain charge	$V_{DD} = 48\text{ V}$, $I_D = 38\text{ A}$, $V_{GS} = 10\text{ V}$	-	43 9 15	58	ns ns ns

1. Pulsed: pulse duration = 300 μs , duty cycle 1.5%

Table 7. Switching times

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$ t_r	Turn-on delay time Voltage rise time	$V_{DD} = 30\text{ V}$, $I_D = 19\text{ A}$, $R_G = 4.7\text{ }\Omega$, $V_{GS} = 10\text{ V}$ (see Figure 14)	-	20 100	-	ns ns
$t_{d(off)}$ t_f	Turn-off delay time Fall time		-	50 20	-	ns ns
$t_{d(off)}$ t_f t_c	Off-voltage rise time Fall time Cross-over time	$V_{clamp} = 48\text{ V}$, $I_D = 38\text{ A}$, $R_G = 4.7\text{ }\Omega$, $V_{GS} = 10\text{ V}$ (see Figure 16)	-	45 42 60	-	ns ns ns

Table 8. Source drain diode

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
I_{SD}	Source-drain current		-		38	A
$I_{SDM}^{(1)}$	Source-drain current (pulsed)		-		152	A
$V_{SD}^{(2)}$	Forward on voltage	$I_{SD} = 38 \text{ A}, V_{GS} = 0$	-		1.5	V
t_{rr}	Reverse recovery time	$I_{SD} = 38 \text{ A}, di/dt = 100 \text{ A}/\mu\text{s}$	-	95		ns
Q_{rr}	Reverse recovery charge	$V_{DD} = 100 \text{ V}, T_j = 150 \text{ }^\circ\text{C}$	-	260		μC
I_{RRM}	Reverse recovery current	(see Figure 16)	-	5.5		A

1. Pulsed: pulse duration = 300 μs , duty cycle 1.5%

2. Pulse width limited by safe operating area.

2.1 Electrical characteristics (curves)

Figure 2. Safe operating area

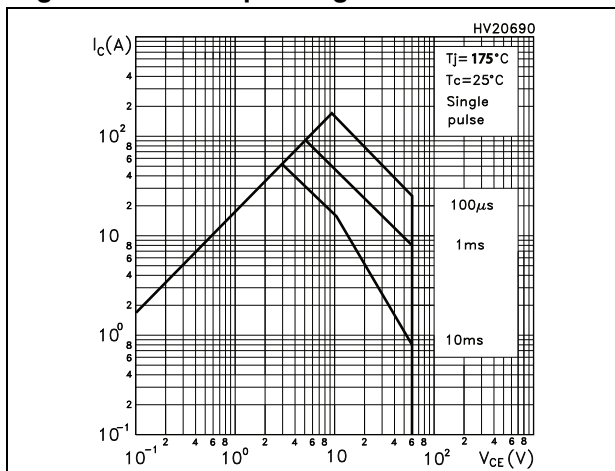


Figure 3. Thermal impedance

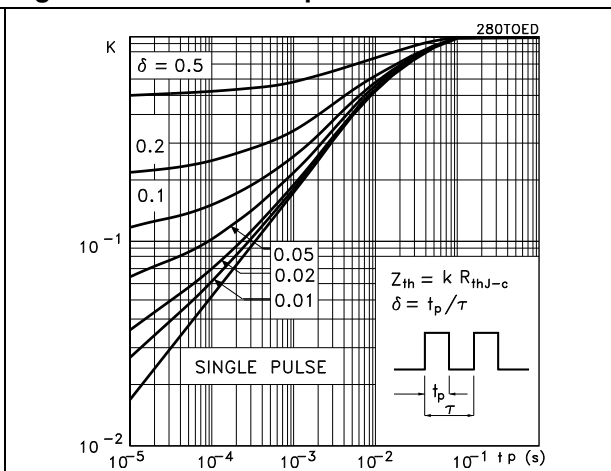


Figure 4. Output characteristics

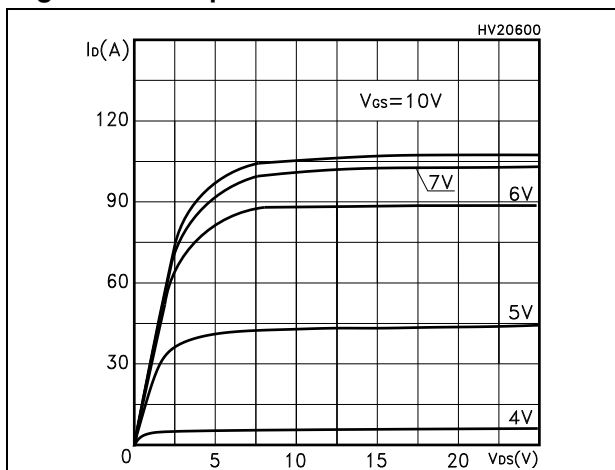


Figure 5. Transfer characteristics

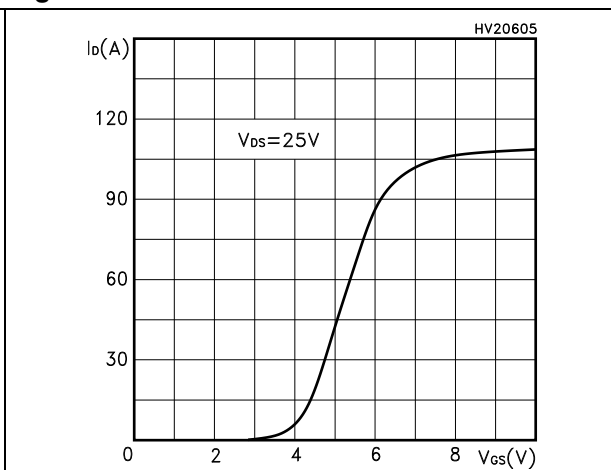


Figure 6. Transconductance

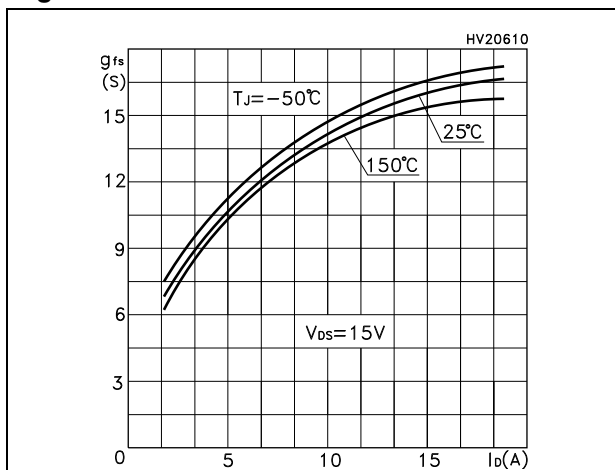


Figure 7. Static drain-source on-resistance

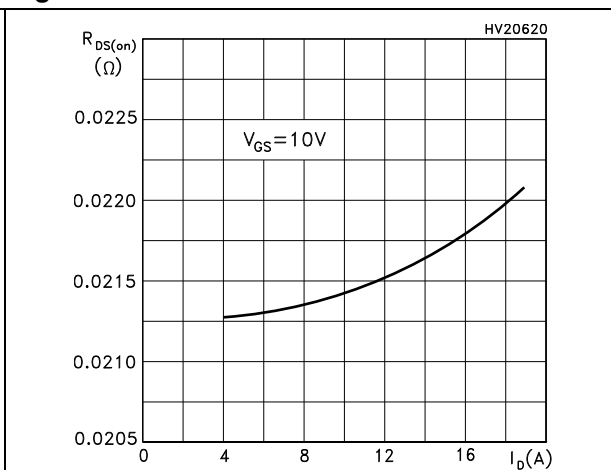


Figure 8. Gate charge vs gate-source voltage Figure 9. Capacitance variations

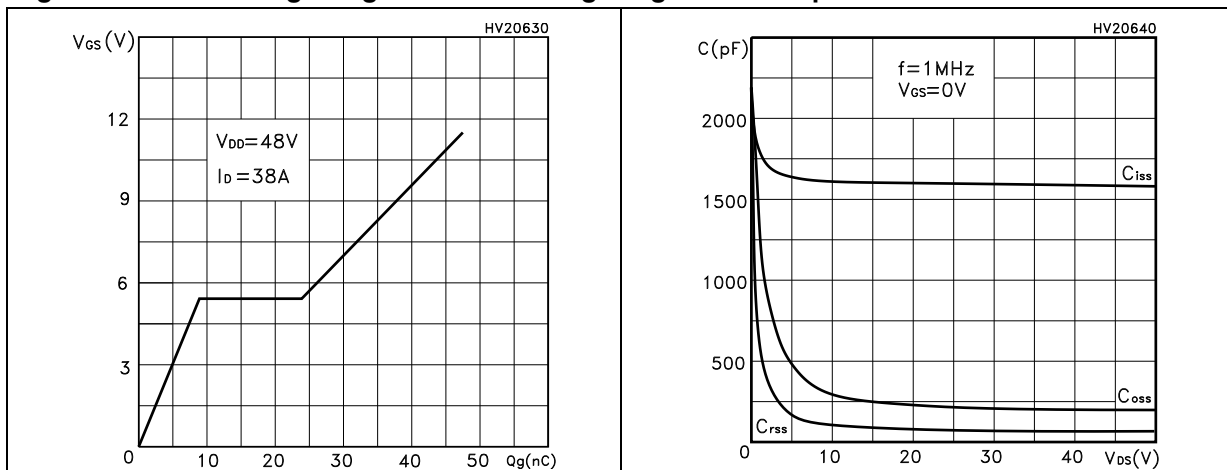


Figure 10. Normalized gate threshold voltage vs temperature Figure 11. Normalized on-resistance vs temperature

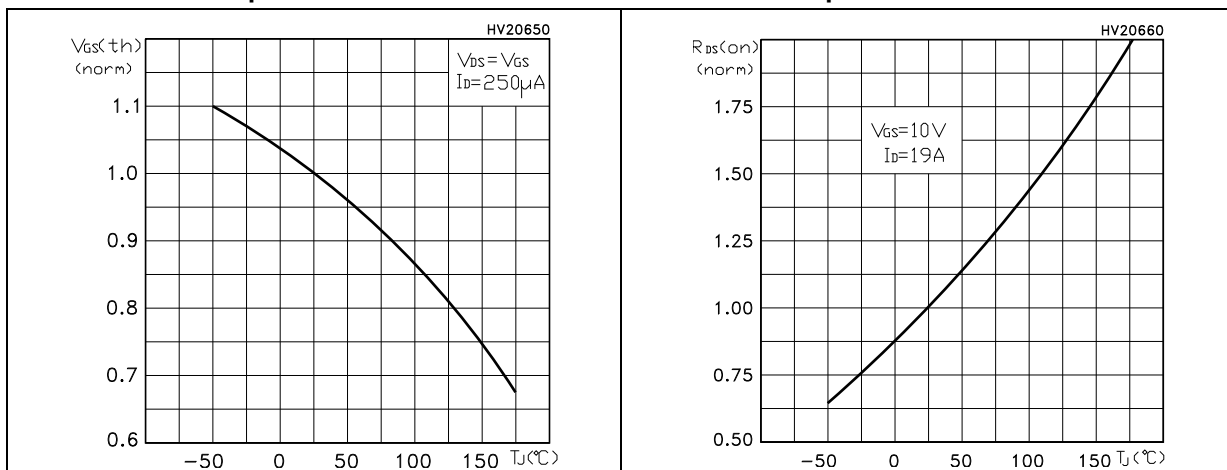
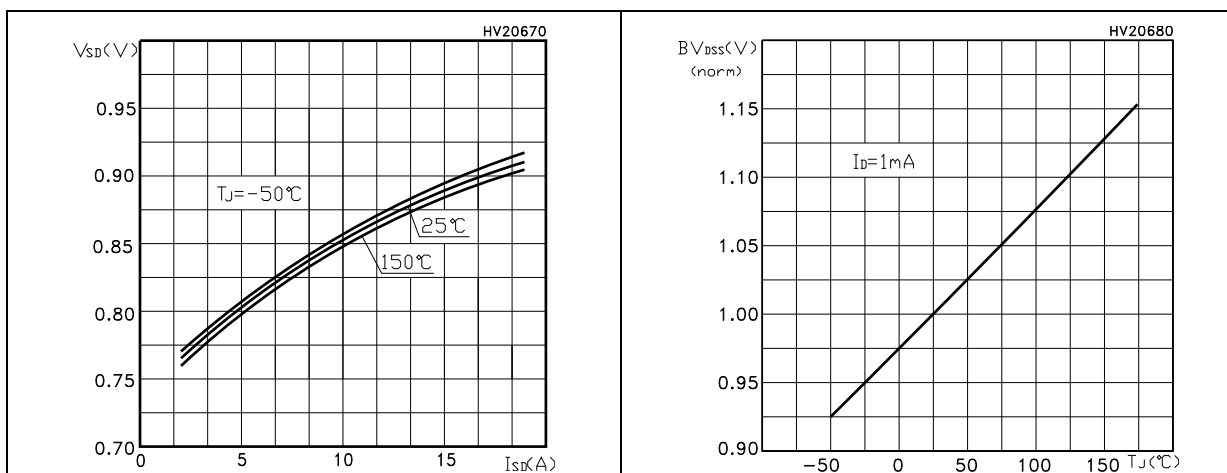
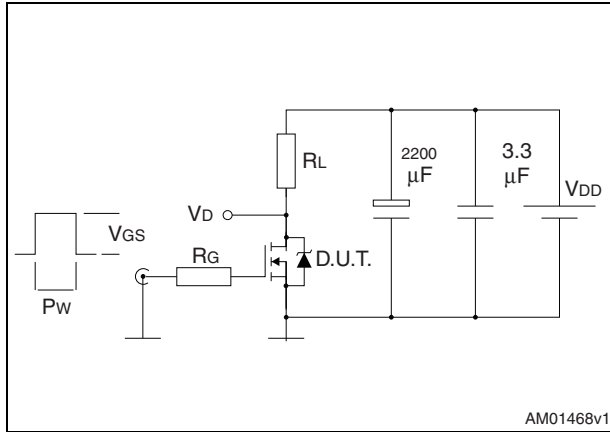


Figure 12. Source-drain diode forward characteristics Figure 13. Normalized $B_{V_{DS}}$ vs temperature



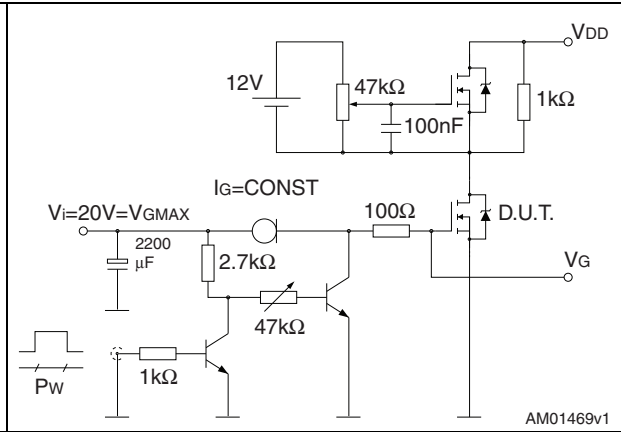
3 Test circuits

Figure 14. Switching times test circuit for resistive load



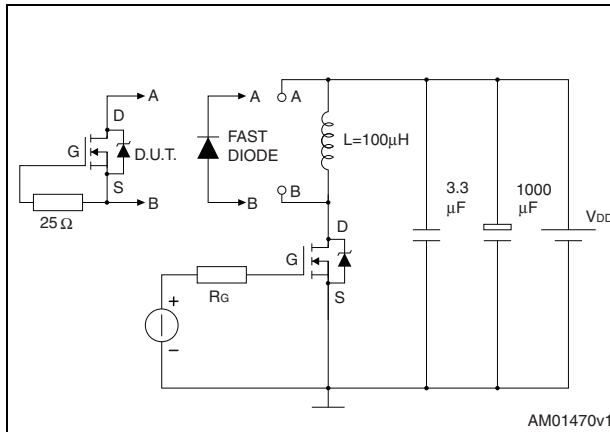
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Figure 15. Gate charge test circuit



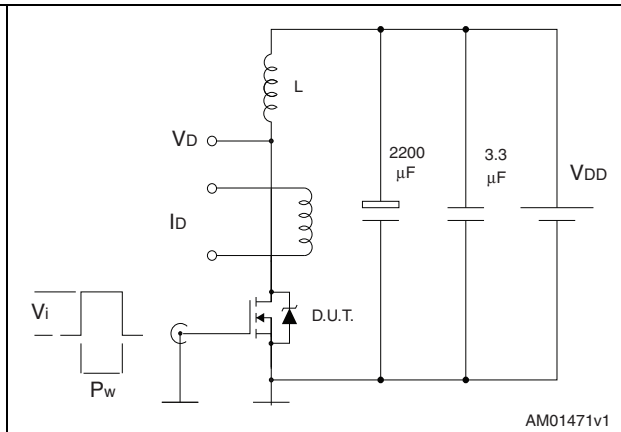
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Figure 16. Test circuit for inductive load switching and diode recovery times



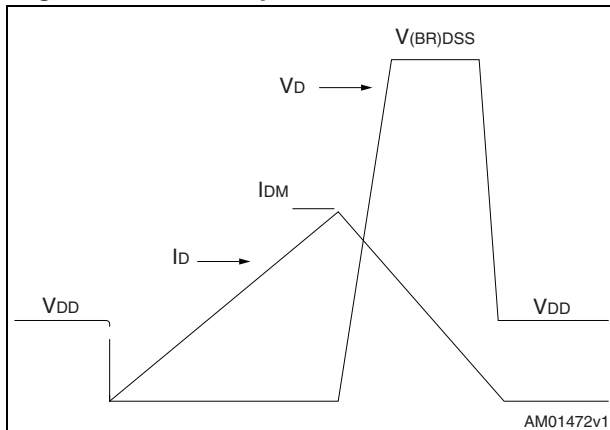
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Figure 17. Unclamped inductive load test circuit



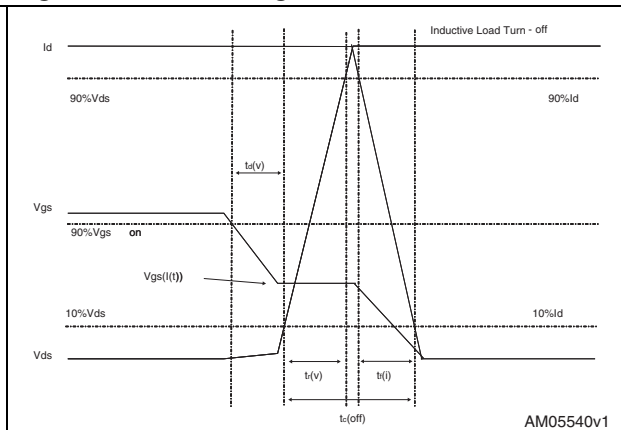
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Figure 18. Unclamped inductive waveform



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Figure 19. Switching time waveform



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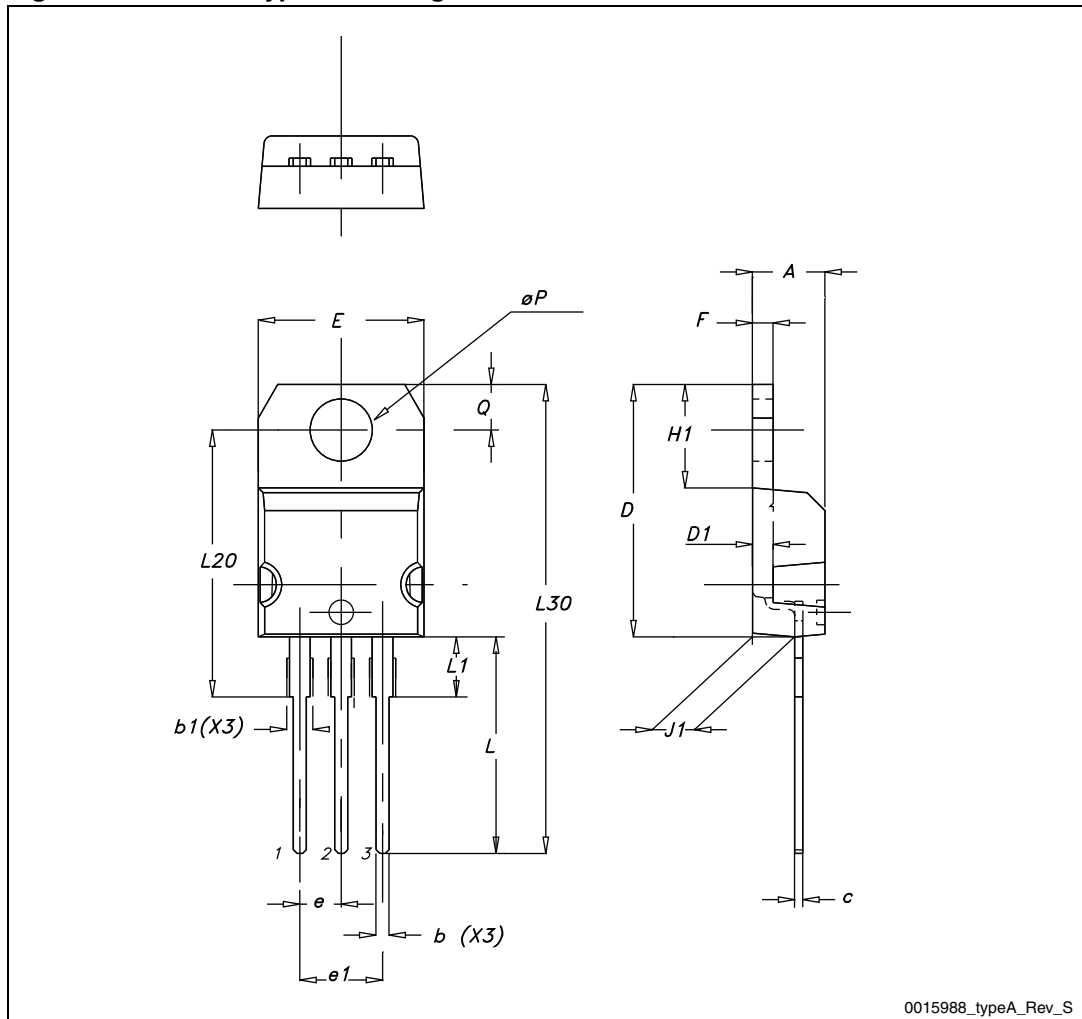
4 Package mechanical data

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Table 9. TO-220 type A mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	4.40		4.60
b	0.61		0.88
b1	1.14		1.70
c	0.48		0.70
D	15.25		15.75
D1		1.27	
E	10		10.40
e	2.40		2.70
e1	4.95		5.15
F	1.23		1.32
H1	6.20		6.60
J1	2.40		2.72
L	13		14
L1	3.50		3.93
L20		16.40	
L30		28.90	
ØP	3.75		3.85
Q	2.65		2.95

Figure 20. TO-220 type A drawing



5 Revision history

Table 10. Revision history

Date	Revision	Changes
09-Sep-2004	1	Preliminary version.
04-Feb-2005	2	Complete version.
17-Aug-2006	3	New template. No content change.
13-Nov-2006	4	Inserted new value.
05-Jul-2010	5	Updated Section 2.1: Electrical characteristics (curves) .
19-Dec-2012	6	Updated: Section 4: Package mechanical data

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